Splitting of Dirac band on Cr₂O₃/Graphene/Ni(111)

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Graphene is one of the most promising Dirac electronic systems. By functionalizing graphene, a sizable local magnetic moments and spin-orbit coupling can be induced in graphene. The main known mechanism responsible for the π band modifications including: the spin-dependent hybridization with the d states of the transition metal (proximity exchange), spin splitting due to inversion symmetry breaking (Bychkov-Rashba splitting) and the sublattice-symmetry breaking (pseudospin splitting). Recently, it has been predicted that a nontrivial band gap opening in the graphene Dirac bands asymmetric between K and K valleys at antiferromagnets Cr₂O₃/graphene interface, which is mediated by symmetry protected boundary magnetization of Cr2O3 and proximity effect induced SOC. The fabrication of this structure has been realized by Picone's group successfully on Ni(111) substrate. Moreover, a narrowed band gap of ultrathin α -Cr₂O₃ than that of crystal was observed by STS. While this progress is impressive, it is recognized that the size of bulk material often largely exceeds the characteristic for inducing a large proximity spin-orbit coupling in graphene. Directly experimental evidence of a Dirac band gap opening induced by Cr₂O₃ is still lack. From this perspective, it is beneficial to direct describe band structure of ultrathin Cr₂O₃/graphene. Here, we report a observable giant π band splitting in ARPES experiment induced by depositing ultrathin Cr₂O₃ film on graphene(Gr)/Ni(111). We speculate the evolution of graphene π band from n-doping-type to splitting-type comes from a nontrivial sublattice-symmetry breaking.



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